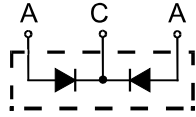
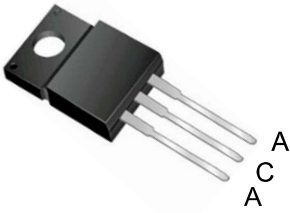




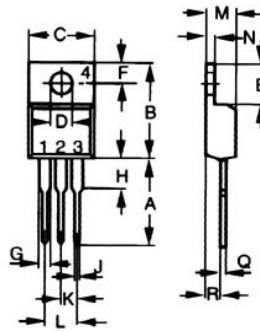
MUR1620FCT to MUR1660FCT

Ultra Fast Recovery Diodes



A=Anode, C=Cathode

Dimensions ITO-220AB



Dim.	Inches		Millimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.550	12.70	13.97
B	0.580	0.630	14.73	16.00
C	0.390	0.420	9.91	10.66
D	0.139	0.161	3.54	4.08
E	0.230	0.270	5.85	6.85
F	0.100	0.125	2.54	3.18
G	0.045	0.065	1.15	1.65
H	0.110	0.230	2.79	5.84
J	0.025	0.040	0.64	1.01
K	0.100	BSC	2.54	BSC
M	0.170	0.190	4.32	4.82
N	0.045	0.055	1.14	1.39
Q	0.014	0.022	0.35	0.56
R	0.090	0.110	2.29	2.79

	V _{RRM}	V _{DC}
	V	V
MUR1620FCT	200	200
MUR1640FCT	400	400
MUR1660FCT	600	600

Rating	Symbol	MUR1620FCT	MUR1640FCT	MUR1660FCT	Unit
Maximum Repetitive Reverse Voltage	V _{RRM}	200	400	600	V
DC Blocking Voltage	V _{DC}	200	400	600	V
Maximum Average Forward Current	I _{AV}	16			A
Peak Forward Surge Current ,8.3ms single half sine-wave superimposed on rated load(JEDEC method)	I _{FSM}	250			A
Maximum Forward Voltage at 8A,per element	V _F	1.05	1.30	1.60	V
Maximum DC Reverse Current at T _A =25°C Rated DC Blocking Voltage T _A =100°C	I _R	1 300			μA
Maximum Reverse Recovery Time (Note 1)	T _{RR}	50			ns
Maximum Thermal Resistance(Note 2)	R _{θ-JC}	6.5			°C/W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to +150			°C

NOTES:

- Reverse Recovery Test Conditions: I_F=.5A, I_R=1A, I_{rr}=.25A.
- Thermal resistance from junction to case.

FEATURES

- * Glass passivated chip
- * Superfast switching time for high efficiency
- * Low forward voltage drop and high current capability
- * Low reverse leakage current
- * High surge capacity



MUR1620FCT to MUR1660FCT

Ultra Fast Recovery Diodes

FIG.1 - FORWARD CURRENT DERATING CURVE

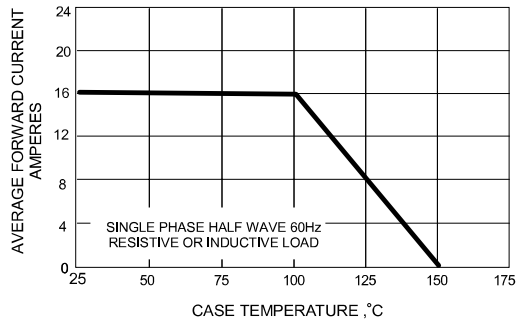


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

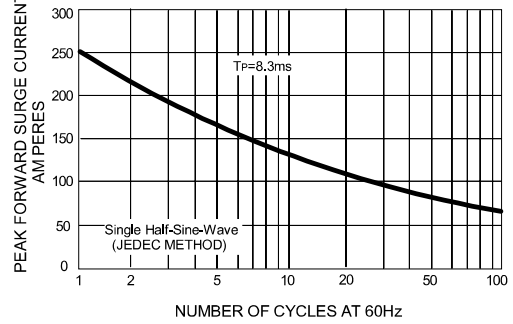


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

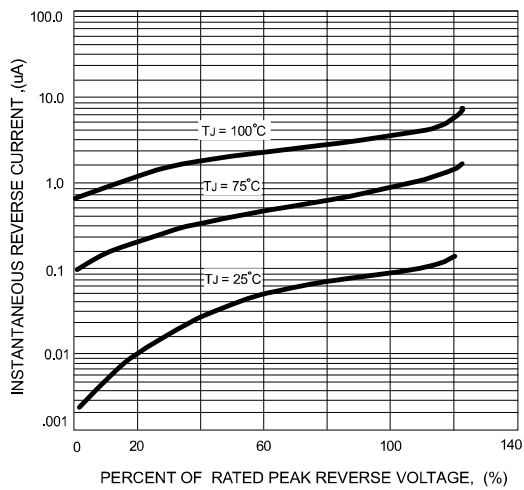


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

